

Abstract

Disclosed are a high-throughput process equipment for film deposition or etching and a method thereof, includes: a reaction chamber, a stage control apparatus and a process isolation apparatus; the stage control apparatus includes a substrate stage and a main stage; the substrate stage is on the main stage, and carries and moves a substrate to be deposited or etched; the main stage carries the substrate stage and moves the substrate stage; the process isolation apparatus provides a process isolation zone above the substrate stage such that processes are carried out only within the process isolation zone, thereby isolating the processes within a local region of the substrate, and in combination with the stage control apparatus, the equipment achieves independent and uniform processes for multiple local regions of the substrate. The equipment has a simple design, widely applicable, easy to use, and can produce highly uniform films and etching profiles.